

# Thermal shock resistance of in situ formed $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$ composites by gelcasting

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## Abstract

Thermal shock resistance of  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites was evaluated by water quenching and subsequent three-point bending tests of strength diminution.  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites which was prepared with in situ liquid pressureless sintering process using  $\text{Yb}_2\text{O}_3$  and  $\text{Al}_2\text{O}_3$  powders as sintering additives by gelcasting showed no macroscopic cracks and the critical temperature difference ( $\Delta T_c$ ) could be up to 1400 °C. A mass of pores existed in the sintered body and the irregular shaped fibers extended from the pores increased the thermal shock property.

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## 1. Introduction

Silicon nitride ( $\text{Si}_3\text{N}_4$ ) ceramics is a suitable material for high temperature missile radome application because of high temperature mechanical strength, good resistance to rain erosion, low dielectric constant and loss, good thermomechanical property [1–9]. However, monolithic  $\text{Si}_3\text{N}_4$  shows catastrophic drops in flexural strength after thermal shock above the critical temperature which cumbered the application. On the other hand, the silicon oxynitride ( $\text{Si}_2\text{N}_2\text{O}$ ) ceramics have been recognized as a promising material for high temperature applications due to their good resistant to oxidation and to thermal shock [10,11]. Moreover, the results show that properly dispersed  $\text{Si}_2\text{N}_2\text{O}$  in  $\text{Si}_3\text{N}_4$  based ceramics can optimize the properties [12]. Therefore,  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  ceramics were fabricated with in situ liquid pressureless sintering process using  $\text{Yb}_2\text{O}_3$  and  $\text{Al}_2\text{O}_3$  powders as sintering additives by gelcasting in the present work. Although the thermal shock property is very important for radome application, no research has been done on thermal shock resistance of  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  ceramics. So, the thermal shock

resistance of  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  ceramics with temperature difference ranging from 500 to 1400 °C, by measuring the flexural strength of the specimen.

## 2. Experimental procedure

### 2.1. Raw materials

As starting materials, the  $\text{Si}_3\text{N}_4$  powder (Beijing Tsinghua Unisp Lendor High Technology Ceramics Co., China,  $d_{50} = 0.5 \mu\text{m}$ ,  $\alpha$  phase 93%), the  $\text{SiO}_2$  (Chengdu Sinuowei Co., Ltd., China,  $d_{50} = 2 \mu\text{m}$ , purify 99.95%) and sintering additives ( $\text{Yb}_2\text{O}_3$  and  $\text{Al}_2\text{O}_3$ ,  $\text{Yb}_2\text{O}_3$  Griem Advanced Materials Co., Ltd.,  $d_{50} = 3.5 \mu\text{m}$ , purify 99.95%,  $\text{Al}_2\text{O}_3$  Zibo Hengji Tianli Co., Ltd., China,  $d_{50} = 1.56 \mu\text{m}$ , purify 99.99%). The microstructures of  $\text{Si}_3\text{N}_4$ ,  $\text{SiO}_2$ ,  $\text{Yb}_2\text{O}_3$  and  $\text{Al}_2\text{O}_3$  are shown in Fig. 1. Raw materials for the mixed AM-MBAM system are listed in Table 1.

### 2.2. Billet fabrication

The schematic forming process of gelcasting is described in Fig. 2. First, the mixture powder of 80 wt.%  $\alpha$ - $\text{Si}_3\text{N}_4$ , 10 wt.%  $\text{SiO}_2$ , 6 wt.%  $\text{Yb}_2\text{O}_3$  and 4 wt.%  $\text{Al}_2\text{O}_3$  powder and 0.25 wt.% dispersant were added to premix solution of organic monomer

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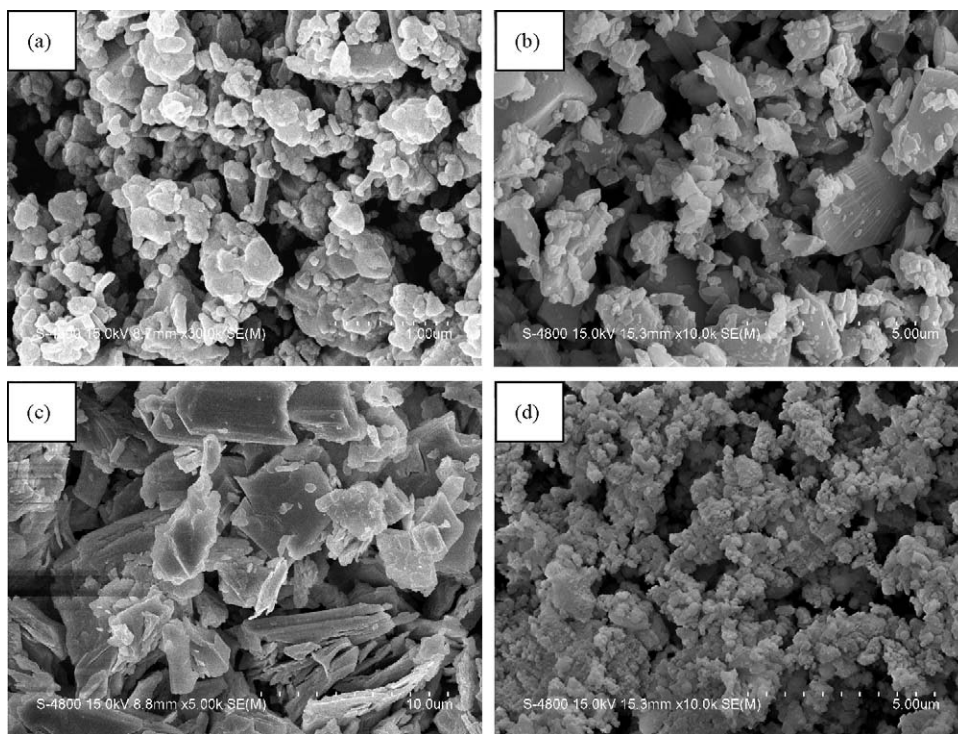


Fig. 1. The microstructure of raw materials: (a)  $\text{Si}_3\text{N}_4$ , (b)  $\text{SiO}_2$ , (c)  $\text{Yb}_2\text{O}_3$  and (d)  $\text{Al}_2\text{O}_3$ .

by mechanical stirring till solids loading up to 45 vol.%. Afterwards, the mixtures were milled for 24 h in a nylon resin jar using alumina ball-milling media to break down agglomerates and to achieve good homogeneity. After degassing for 8–10 min in a rotary evaporator under vacuum, the initiator and catalyst were applied to the slurry. Then it was cast into metal mould at room temperature. The mould was kept at temperature of 60–80 °C, and the consolidation of suspension formed a green body. After consolidation, the green bodies were demolded and dried under controlled humidity to avoid cracking and non-uniform shrinkage due to rapid drying. Binder burnout was carried out at 600 °C for 2 h, with a heating rate of 2 °C/min and a natural cooling. Then the samples were embedded in 50 wt.%  $\text{Si}_3\text{N}_4$  + 40 wt.% BN + 10 wt.%  $\text{Al}_2\text{O}_3$  powder bed in a graphite crucible and sintered to the temperature of 1680 °C for 1.5 h in  $\text{N}_2$  atmosphere, followed by natural cooling under  $\text{N}_2$  gas atmosphere.

### 2.3. Specimen preparation

The thermal shock resistance was determined by measuring the flexural strength of water-quenched specimen. Specimens

were machined into a bar shape with dimensions of 3 mm × 4 mm × 36 mm. The bars were ground with a diamond wheel and polished using diamond pastes. The final diamond lap had an abrasive particle of size 3 μm before fracture strength testing and the specimen edges were slightly beveled on a 1200-grit emery paper to remove notches introduced in the course of machining.

### 2.4. Thermal shock experiments

The thermal shock resistance was carried out in a vertical tube furnace at temperatures between 500 and 1400 °C in air. Ground and polished rectangular bars for thermal shock testing were heated to the desired temperatures and held for 30 min in a furnace before quenching by dropping into a bath of the mixture of water and ice.

### 2.5. Mechanical test and characterization

The flexural strengths of bars after thermal shock were examined at room temperature by three-point flexure test with a span of 30 mm at a loading rate of 0.5 mm/min. Six samples

Table 1  
Raw materials for the AM-MBAM system.

Function	Raw material	Manufacturer
Monomer	Acrylamide (AM)	Aldrich, USA
Crosslinker	<i>N,N'</i> -Methylenebisacrylamide (MBAM)	Hongxing Biological and Chemical Factory of Beijing, China
Catalyst	<i>N,N,N',N'</i> -Tetramethylethylenediamine (TEMED)	Beijing Chemical Reagent Company, China
Initiator	Ammonium persulphate (APS)	Beijing Third Reagent Works, China
Dispersant	Tetramethylammoniumhydroxide solution	Beijing Chemical Reagent Company, China
Solvent	Deionized water	

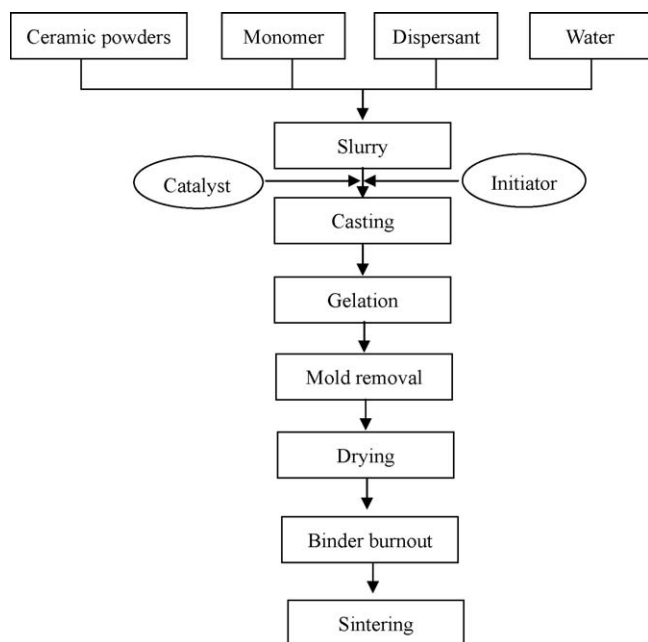


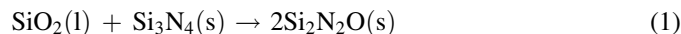
Fig. 2. The gelcasting process flow chart.

were used to calculate the average values and dispersion. Young's modulus was measured by using the pulse echo method. To identify the phase of the samples, XRD (Cu K $\alpha$ , D/MAX-250, Rigaku, Japan) technique was employed on the polished surfaces. Meanwhile, microstructure analysis of the surfaces of the samples, which were polished with diamond pastes and etched with melting NaOH at 400 °C for 1.5 min, was carried out by scanning electron microscopy (SEM). The porosity of the sample was measured by the mercury porosimetry. The microstructure, pore size, pore distribution and morphology of the fibers in the porous Si<sub>2</sub>N<sub>2</sub>O–Si<sub>3</sub>N<sub>4</sub> bodies of the cross-section were also observed by SEM.

### 3. Results and discussion

#### 3.1. The Si<sub>2</sub>N<sub>2</sub>O phase formation

Fig. 3 showed the XRD profiles of the sample. It could be revealed that Si<sub>3</sub>N<sub>4</sub> as well as Si<sub>2</sub>N<sub>2</sub>O phases were all existed. It was the reaction between Si<sub>3</sub>N<sub>4</sub> and SiO<sub>2</sub> according to:



It is thermodynamically possible to form Si<sub>2</sub>N<sub>2</sub>O from SiO<sub>2</sub> and  $\alpha$ -Si<sub>3</sub>N<sub>4</sub> or  $\beta$ -Si<sub>3</sub>N<sub>4</sub> according to the reaction. The formation of Si<sub>2</sub>N<sub>2</sub>O indeed proceeds in a liquid phase. The Si<sub>2</sub>N<sub>2</sub>O crystal structure is built up by distorted [SiN<sub>3</sub>O] tetrahedral, whereas  $\alpha$ - and  $\beta$ -Si<sub>3</sub>N<sub>4</sub> are composed of [SiN<sub>4</sub>] tetrahedron is replaced by an oxygen atom, a tetrahedral [SiN<sub>3</sub>O] structural unit of Si<sub>2</sub>N<sub>2</sub>O is formed. Therefore, the Si<sub>2</sub>N<sub>2</sub>O nuclei are formed in the liquid phase at the sintering temperature. After the Si<sub>2</sub>N<sub>2</sub>O nucleation occurs, Si<sub>2</sub>N<sub>2</sub>O grain-growth rate is very high. Si<sub>2</sub>N<sub>2</sub>O grew via a solution-precipitation process in the presence of a large amount of SiO<sub>2</sub>-rich liquid phase. Obviously, the liquid phases were largely consumed with the formation of the crystalline Si<sub>2</sub>N<sub>2</sub>O.

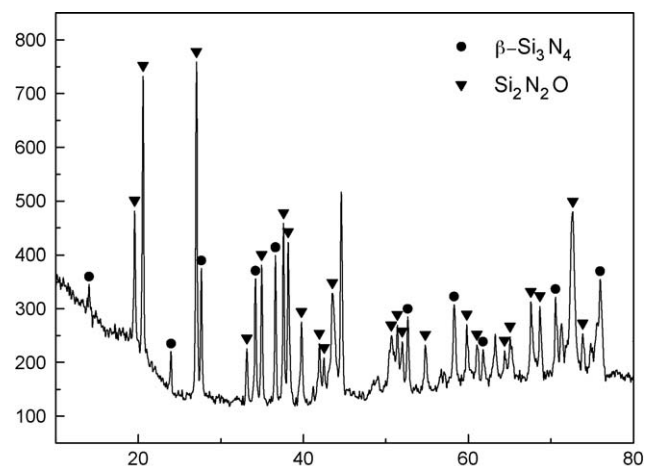


Fig. 3. The XRD profiles of the sample.

#### 3.2. The thermal shock resistance

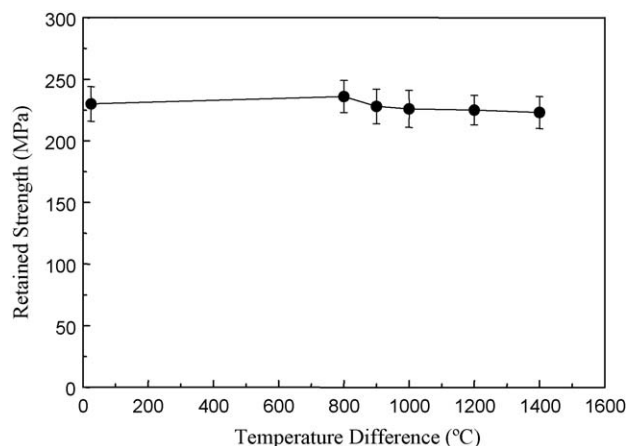
To evaluate the thermal stress crack initiation and propagation behavior of ceramics, two thermal shock resistance parameters are usually used. According to the theory of critical stress by Kingery [13], the residual strength of material after water quenching is an important index of the thermal shock resistance. Thermal stress fracture resistance parameter  $R$  is introduced to estimate thermal stress fracture resistance of materials:

$$\Delta T_{\max} = R = \sigma_f \frac{(1 - \nu)}{E\alpha} \quad (2)$$

where  $\sigma_f$  is the flexural strength,  $\nu$  is the Poisson ratio,  $E$  is the Young's modulus of elasticity,  $\alpha$  is the coefficient of thermal expansion.

Hasselmann [14] proposed that the driving force for crack propagation is provided by the elastic energy stored at cracks. The thermal stress damage resistance parameter,  $R^{IV}$ , represented by

$$R^{IV} = \frac{E\gamma_f}{\sigma^2(1 - \nu)} \approx \frac{(K_{IC}/\sigma)^2}{(1 - \nu)} \quad (3)$$

Fig. 4. Flexural strength of Si<sub>2</sub>N<sub>2</sub>O–Si<sub>3</sub>N<sub>4</sub> ceramic after thermal shock with temperature difference ( $\Delta T$ ).

where  $\gamma_f$  is the fracture surface energy and  $K_{IC}$  is the fracture toughness.  $R^{IV}$  decides the resistance to catastrophic crack propagation of ceramics under a critical temperature difference.

According to the above two equations, it can be clearly seen that the thermal shock resistance can be improved by the increase of the flexural strength and fracture toughness or decrease of Young's modulus and coefficient of thermal expansion.

In the current work, the thermal shock resistance was observed by measuring the flexural strength after thermal shock test, as shown in Fig. 4. It is well known that the traditional thermal shock behavior of monolithic  $\text{Si}_3\text{N}_4$  is as one of the brittle materials [15]. That is, the flexural strength decreases rapidly after thermal shock with temperature difference. However, the flexural strength of  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  ceramic after thermal shock test was not changed much, showing the excellent thermal shock resistance. Moreover, there was no critical temperature ( $\Delta T$ ), at which the strength decreases catastrophically, up to 1400 °C.

### 3.3. The microstructure and discussion

The excellent thermal shock property of the in situ  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  ceramic could be explained as follows.

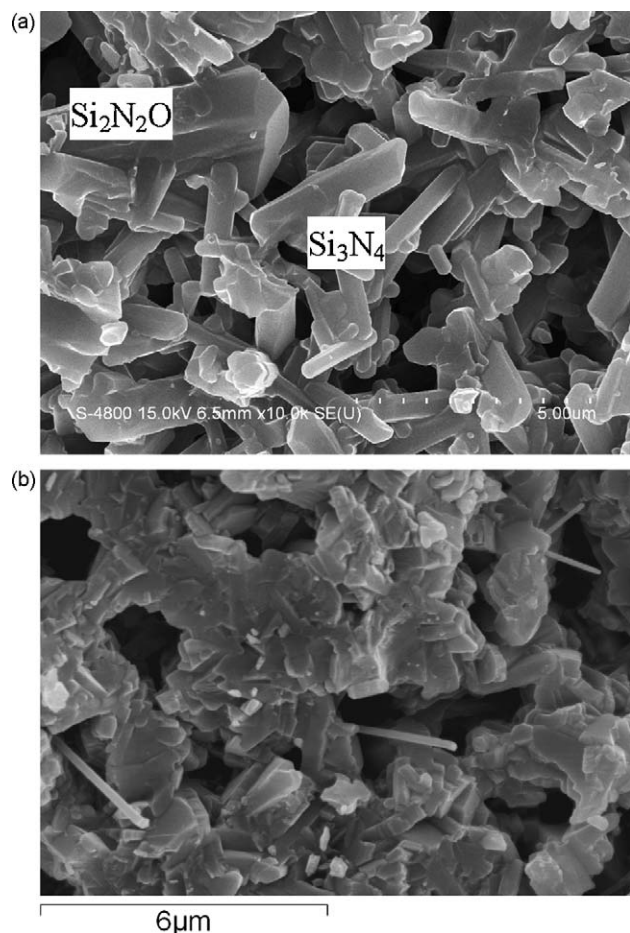


Fig. 5. SEM photograph of the  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites (a) surface and (b) cross-section.

Firstly, the most important reason for the improving resistance of the materials was the formation of in situ  $\text{Si}_2\text{N}_2\text{O}$  which dispersed in silicon nitride matrix ceramics. Fig. 5(a) showed SEM photograph of surface of the  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites. The composites were comprised of rod  $\beta$ - $\text{Si}_3\text{N}_4$  and plate  $\text{Si}_2\text{N}_2\text{O}$  phases. Compared to  $\text{Si}_3\text{N}_4$  ceramics (The Young's modulus was 280 GPa),  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites possessed low Young's modulus  $E$ , which was 125 GPa and the fracture toughness could be improved when the  $\text{Si}_2\text{N}_2\text{O}$  dispersed in the  $\beta$ - $\text{Si}_3\text{N}_4$  matrix grains [12]. So due to the  $\text{Si}_2\text{N}_2\text{O}$  phase, the change trends of the mechanical properties improved the thermal shock resistance of in situ  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites.

Secondly, the residual pores had great influence on the thermal shock resistance of composites. Fig. 5(b) showed SEM photograph of cross-section of the  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites. It could be seen that there existed amount of pores that distributed evenly in the matrix and the diameters of the pores were about 3 μm and the porosity was 27%. The pores in composites could be distributed to act as crack stoppers. The thermal shock resistance of ceramics was improved greatly due to the porosity. In the porous microstructure, the irregular shaped  $\text{Si}_2\text{N}_2\text{O}$  fibers extended from the pores. The diameters of the  $\text{Si}_2\text{N}_2\text{O}$  fibers were about 50–100 nm. Some  $\text{Si}_2\text{N}_2\text{O}$  fibers showed wavy and rough surface due to the formation of several nucleation sites. The fibers extended from the pores dissipated the energy of crack growth and contributed to the improvement of the thermal shock property.

### 4. Conclusion

In this study, the in situ  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites were prepared via gelcasting and pressureless sintering. The  $\text{Si}_2\text{N}_2\text{O}$ – $\text{Si}_3\text{N}_4$  composites had excellent thermal shock resistance and the critical temperature difference ( $\Delta T_c$ ) can be up to 1400 °C. The excellent thermal shock resistances were attributed to the  $\text{Si}_2\text{N}_2\text{O}$  phase which dissipated the energy of crack growth, and the residual pores and the fibers extended from the pores acted as a stopper to the crack.

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